

STD790AT4

Medium Current, High Performance, Low Voltage PNP Transistor

General features

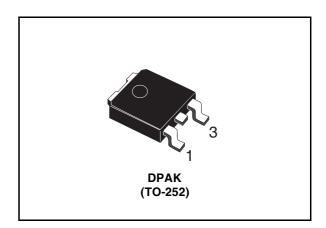
- Very low Collector to Emitter saturation voltage
- D.C. Current gain, h_{FE} >100
- 3A continuous collector current
- 40V breakdown voltage (V_{(BR)CER})
- Surgace mounting DPAK(TO-252) power package in tape & reel packing
- In compliance with the 2002/93/EC European Directive

Description

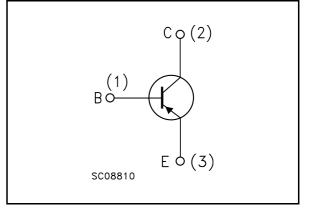
The device in manufactured in low voltage PNP Planar Technology by using a "Base Island" layout. The resulting transistor shows exceptional high gain performance coupled with very low saturation voltage.

Applications

- Power management in portable equipment
- Voltage regulation in bias supply circuits
- Switching regulator in battery charger applications
- Heavy load driver



Internal schematic diagram



Order codes

Part Number	Marking	Package	Packing	
STD790AT4	D790A	DPAK	Tape & reel	

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Electrical ratings

Table 1. Absolute maximum rating	Table 1.	Absolute maximum rating
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Symbol	Parameter	Value	Unit
V _{CBO}	Collector-base voltage (I _E = 0)	-40	V
V _{CER}	Collector-emitter voltage ($R_{BE} = 47\Omega$)	-40	V
V _{CEO}	Collector-emitter voltage $(I_B = 0)$	-30	V
V _{EBO}	Emitter-base voltage (I _C = 0)	-5	V
۱ _C	Collector current	-3	А
I _{CM}	Collector peak current (t _P < 5ms)	-6	А
P _{tot}	Total dissipation at $T_c = 25^{\circ}C$	15	W
T _{stg}	Storage temperature	-65 to 150	°C
Τ _J	Max. operating junction temperature	150	°C

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R _{thj-case}	Thermal resistance junction-case max	8.33	°C/W



2 Electrical characteristics

 $(T_{case} = 25^{\circ}C \text{ unless otherwise specified})$

Table 3.	Electrical characteristics						
Symbol	Parameter	Test Co	nditions	Min.	Тур.	Max.	Unit
I _{CBO}	Collector cut-off current (I _E =0)	V _{CB} = -30V V _{CB} = -30V;	T _C = 100°C			-10 100	μΑ μΑ
I _{EBO}	Emitter cut-off current (I _C =0)	$V_{PP} = -4V$				-10	μA
V _{(BR)CEO} ⁽²⁾	Collector-emitter breakdown voltage $I_{C} = -10$ mA $(I_{B} = 0)$		-30			V	
V _{(BR)CER} ⁽²⁾	Collector-emitter breakdown voltage $(R_{BE} = 47\Omega)$	I _C = -10mA		-40			v
V _{(BR)CBO}	Collector-base breakdown voltage (I _E =0)	Ι _C = -100μΑ		-40			v
V _{(BR)EBO}	Emitter-base breakdown voltage (I _C =0)	I _E = -100μA		-5			V
V _{CE(sat)} ⁽²⁾	Collector-emitter	I _C = -0.5A	I _B = -5mA			-0.15	V
VCE(sat)	saturation voltage	I _C = -1.2A	I _B = -20mA			-0.25	V
	Ŭ	I _C = -2A	I _B = -20mA			-0.5	V
		I _C = -3A	I _B = -100mA			-0.7	V
		I _C = -3A T _J = 100°C	I _B = -100mA			-0.9	V
V _{BE(sat)} ⁽²⁾	Base-emitter saturation voltage	I _C = -1A	I _B = -10mA		-0.8	-1	V
V _{BE(on)} ⁽²⁾	Base-emitter on voltage	I _C = -1A	$V_{CE} = -2V$		-0.8	-1	۷
		I _C = -10mA	$V_{CE} = -2V$	100	200	400	
		I _C = -500mA	$V_{CE} = -2V$	100	200	400	
h _{FE} ⁽²⁾	DC current gain	I _C = -1A	$V_{CE} = -2V$	100			
		I _C = -2A	$V_{CE} = -1V$	100	160		
		I _C = -3A	$V_{CE} = -1V$	90	130		

Table 3. Electrical characteristics



Tuble 0.						
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
f _t	Transition frequency	$I_{C} = -50 \text{mA}$ $V_{CE} = -5 \text{V}$ f = 50MHz		100		MHz
t _d t _r	Resistive load Delay time Rise time	$I_{C} = -3A$ $V_{CC} = -20V$ $I_{B1} = -I_{B2} = -60mA$		180 160	220 210	ns ns
t _s t _f	Storage time Fall time	(see figure 7)		250 80	300 100	ns ns

 Table 3.
 Electrical characteristics

Note (2) Pulsed duration = 300 μ s, duty cycle \leq 1.5%

2.1 Electrical characteristics (curves)

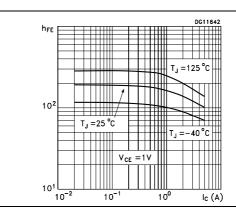


Figure 1. DC current gain

Figure 2. DC current gain

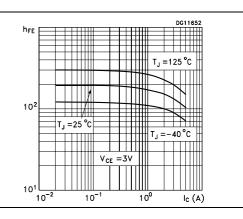
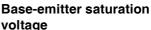
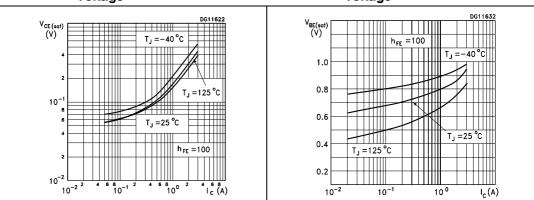


Figure 3. Collector-emitter saturation Figure 4. Base-em voltage voltage







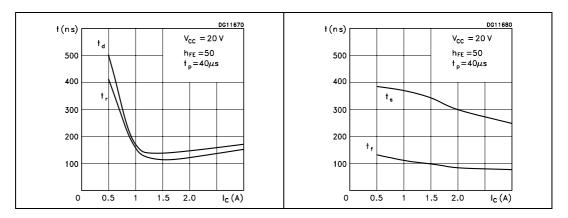
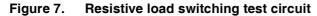
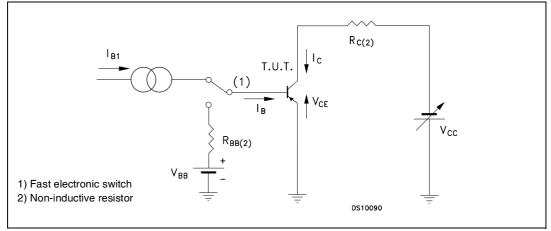


Figure 5. Switching time resistive load Figure 6. Switching time resistive load

2.2 Test circuits





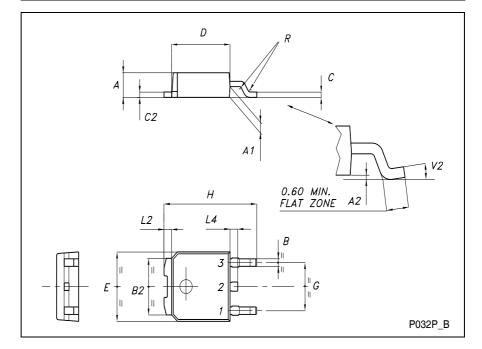
3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com



DIM.	mm			inch			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Α	2.20		2.40	0.087		0.094	
A1	0.90		1.10	0.035		0.043	
A2	0.03		0.23	0.001		0.009	
В	0.64		0.90	0.025		0.035	
B2	5.20		5.40	0.204		0.213	
С	0.45		0.60	0.018		0.024	
C2	0.48		0.60	0.019		0.024	
D	6.00		6.20	0.236		0.244	
Е	6.40		6.60	0.252		0.260	
G	4.40		4.60	0.173		0.181	
Н	9.35		10.10	0.368		0.398	
L2		0.8			0.031		
L4	0.60		1.00	0.024		0.039	
V2	0°		8°	0°		0°	

TO-252 (DPAK) MECHANICAL DATA





4 Revision history

Date	Revision	Changes	
24-Mar-2004	1	Initial release.	
27-Mar-2006	2	New template, new graphics	



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